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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-pqg208">https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-pqg208</a>

## Low Power Modes Overview

Table 2-2 summarizes the low power modes that achieve power consumption reduction when the FPGA or system is idle.

**Table 2-2 • Power Modes Summary**

Mode		VCCI	VCC	Core	Clocks	ULSICC Macro	To Enter Mode	To Resume Operation	Trigger
Active		On	On	On	On	N/A	Initiate clock	None	–
Static	Idle	On	On	On	Off	N/A	Stop clock	Initiate clock	External
	Flash*Freeze type 1	On	On	On	On*	N/A	Assert FF pin	Deassert FF pin	External
	Flash*Freeze type 2	On	On	On	On*	Used to enter Flash*Freeze mode	Assert FF pin and assert LSICC	Deassert FF pin	External
Sleep		On	Off	Off	Off	N/A	Shut down VCC	Turn on VCC supply	External
Shutdown		Off	Off	Off	Off	N/A	Shut down VCC and VCCI supplies	Turn on VCC and VCCI supplies	External

\* External clocks can be left toggling while the device is in Flash\*Freeze mode. Clocks generated by the embedded PLL will be turned off automatically.

## Static (Idle) Mode

In Static (Idle) mode, none of the clock inputs is switching, and static power is the only power consumed by the device. This mode can be achieved by switching off the incoming clocks to the FPGA, thus benefitting from reduced power consumption. In addition, I/Os draw only minimal leakage current. In this mode, embedded SRAM, I/Os, and registers retain their values so the device can enter and exit this mode just by switching the clocks on or off.

If the device-embedded PLL is used as the clock source, Static (Idle) mode can easily be entered by pulling the PLL POWERDOWN pin LOW (active Low), which will turn off the PLL.

Table 2-4 summarizes the Flash\*Freeze mode implementations.

**Table 2-4 • Flash\*Freeze Mode Usage**

Flash*Freeze Mode Type	Description	Flash*Freeze Pin State	Instantiate ULSICC Macro	LSICC Signal	Operating Mode
1	Flash*Freeze mode is controlled only by the FF pin.	Deasserted	No	N/A	Normal operation
		Asserted	No	N/A	Flash*Freeze mode
2	Flash*Freeze mode is controlled by the FF pin and LSICC signal.	"Don't care"	Yes	Deasserted	Normal operation
		Deasserted	Yes	"Don't care"	Normal operation
		Asserted	Yes	Asserted	Flash*Freeze mode

*Note:* Refer to Table 2-3 on page 26 for Flash\*Freeze pin and LSICC signal assertion and deassertion values.

## IGLOO, ProASIC3L, and RT ProASIC3 I/O State in Flash\*Freeze Mode

In IGLOO and ProASIC3L devices, when the device enters Flash\*Freeze mode, I/Os become tristated. If the weak pull-up or pull-down feature is used, the I/Os will maintain the configured weak pull-up or pull-down status. This feature enables the design to set the I/O state to a certain level that is determined by the pull-up/-down configuration.

Table 2-5 shows the I/O pad state based on the configuration and buffer type.

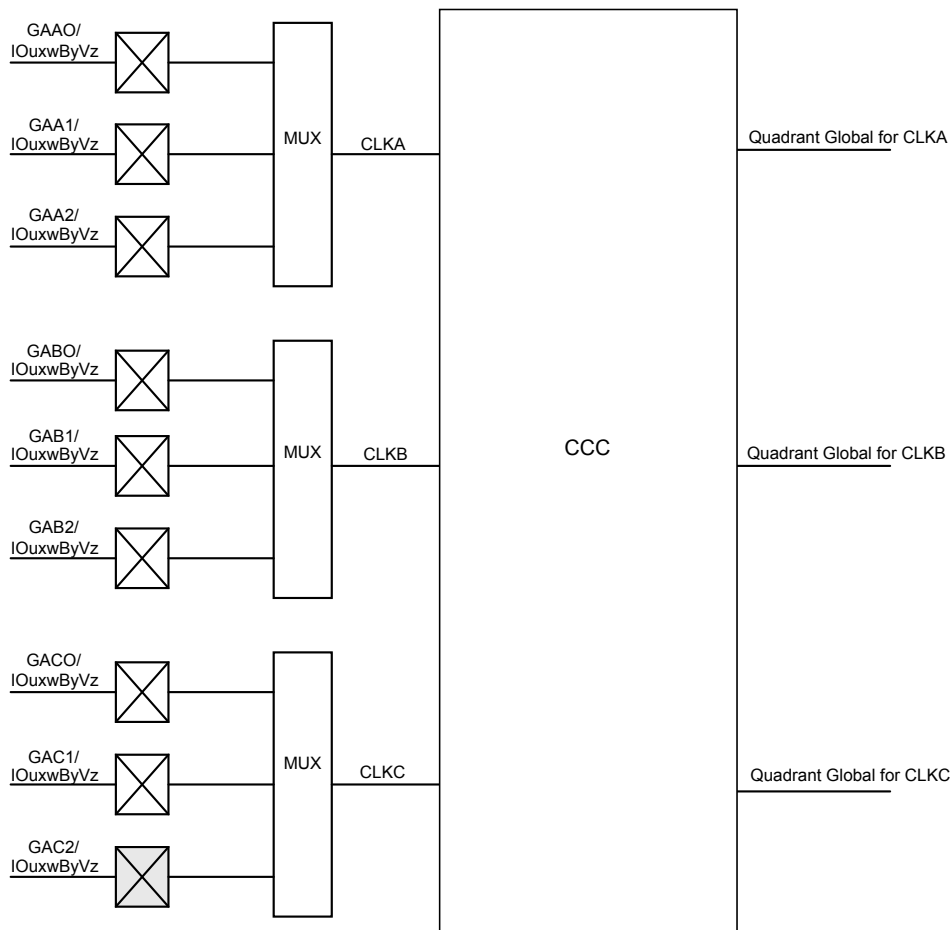
Note that configuring weak pull-up or pull-down for the FF pin is not allowed. The FF pin can be configured as a Schmitt trigger input in IGLOOe, IGLOO nano, IGLOO PLUS, and ProASIC3EL devices.

**Table 2-5 • IGLOO, ProASIC3L, and RT ProASIC3 Flash\*Freeze Mode (type 1 and type 2)—I/O Pad State**

Buffer Type		I/O Pad Weak Pull-Up/-Down	I/O Pad State in Flash*Freeze Mode
Input/Global		Enabled	Weak pull-up/pull-down*
		Disabled	Tristate*
Output		Enabled	Weak pull-up/pull-down
		Disabled	Tristate
Bidirectional / Tristate Buffer	E = 0 (input/tristate)	Enabled	Weak pull-up/pull-down*
		Disabled	Tristate*
	E = 1 (output)	Enabled	Weak pull-up/pull-down
		Disabled	Tristate

\* Internal core logic driven by this input/global buffer will be tied High as long as the device is in Flash\*Freeze mode.

Figure 3-6 shows all nine global inputs for the location A connected to the top left quadrant global network via CCC.



**Figure 3-6 • Global Inputs**

Since each bank can have a different I/O standard, the user should be careful to choose the correct global I/O for the design. There are 54 global pins available to access 18 global networks. For the single-ended and voltage-referenced I/O standards, you can use any of these three available I/Os to access the global network. For differential I/O standards such as LVDS and LVPECL, the I/O macro needs to be placed on (A0, A1), (B0, B1), (C0, C1), or a similar location. The unassigned global I/Os can be used as regular I/Os. Note that pin names starting with GF and GC are associated with the chip global networks, and GA, GB, GD, and GE are used for quadrant global networks. Table 3-2 on page 54 and Table 3-3 on page 55 show the general chip and quadrant global pin names.



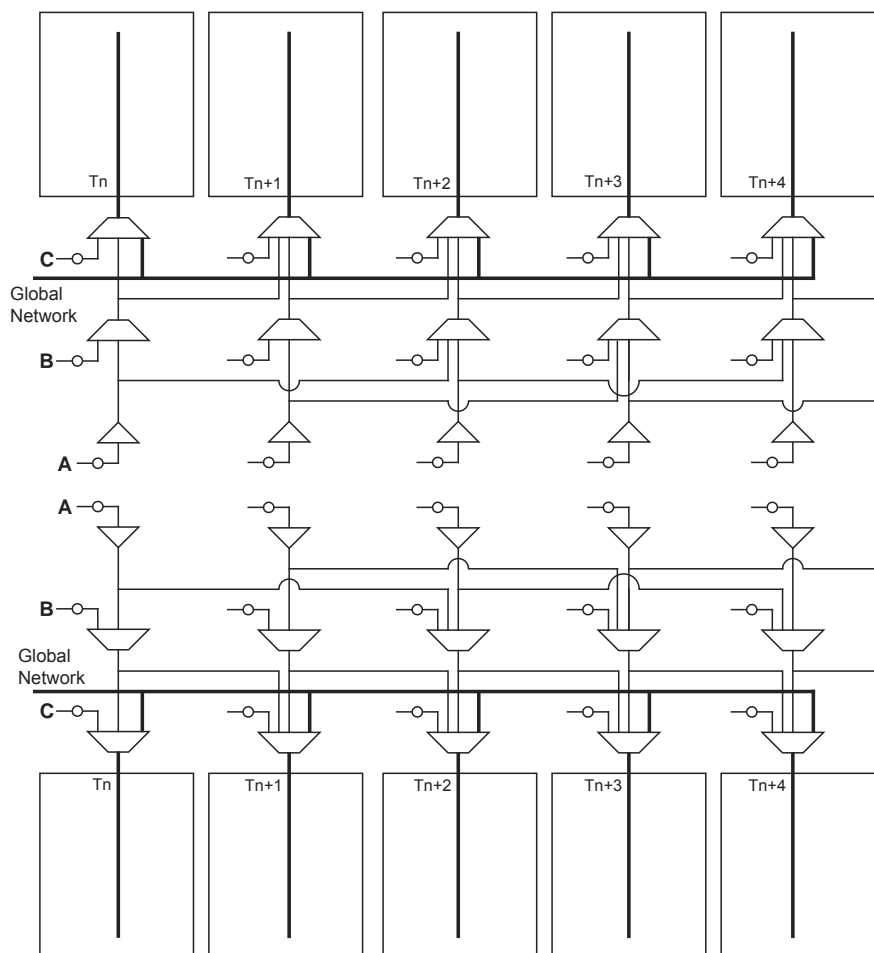
**Table 3-3 • Quadrant Global Pin Name**

I/O Type	Beginning of I/O Name	Notes
Single-Ended	GAAO/IOuxwByVz GAA1/IOuxwByVz GAA2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time
	GABO/IOuxwByVz GAB1/IOuxwByVz GAB2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time.
	GAC0/IOuxwByVz GAC1/IOuxwByVz GAC2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time.
	GBAO/IOuxwByVz GBA1/IOuxwByVz GBA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GBBO/IOuxwByVz GBB1/IOuxwByVz GBB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GBC0/IOuxwByVz GBC1/IOuxwByVz GBC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDAO/IOuxwByVz GDA1/IOuxwByVz GDA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDBO/IOuxwByVz GDB1/IOuxwByVz GDB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDC0/IOuxwByVz GDC1/IOuxwByVz GDC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEAO/IOuxwByVz GEA1/IOuxwByVz GEA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEBO/IOuxwByVz GEB1/IOuxwByVz GEB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEC0/IOuxwByVz GEC1/IOuxwByVz GEC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.

*Note:* Only one of the I/Os can be directly connected to a quadrant at a time.

## Spine Access

The physical location of each spine is identified by the letter T (top) or B (bottom) and an accompanying number ( $Tn$  or  $Bn$ ). The number  $n$  indicates the horizontal location of the spine; 1 refers to the first spine on the left side of the die. Since there are six chip spines in each spine tree, there are up to six spines available for each combination of T (or B) and  $n$  (for example, six T1 spines). Similarly, there are three quadrant spines available for each combination of T (or B) and  $n$  (for example, four T1 spines), as shown in Figure 3-7.



**Figure 3-7 • Chip Global Aggregation**

A spine is also called a local clock network, and is accessed by the dedicated global MUX architecture. These MUXes define how a particular spine is driven. Refer to Figure 3-8 on page 60 for the global MUX architecture. The MUXes for each chip global spine are located in the middle of the die. Access to the top and bottom chip global spine is available from the middle of the die. There is no control dependency between the top and bottom spines. If a top spine, T1, of a chip global network is assigned to a net, B1 is not wasted and can be used by the global clock network. The signal assigned only to the top or bottom spine cannot access the middle two rows of the architecture. However, if a spine is using the top and bottom at the same time (T1 and B1, for instance), the previous restriction is lifted.

The MUXes for each quadrant global spine are located in the north and south sides of the die. Access to the top and bottom quadrant global spines is available from the north and south sides of the die. Since the MUXes for quadrant spines are located in the north and south sides of the die, you should not try to drive T1 and B1 quadrant spines from the same signal.

## Using Spines of Occupied Global Networks

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 61) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

For example, if you want to limit the CLK1\_c signal to the left half of the chip and want to use the right side of the same global network for CLK2\_c, you can add the following PDC commands:

```
define_region -name region1 -type inclusive 0 0 34 29
assign_net_macros region1 CLK1_c
assign_local_clock -net CLK2_c -type chip B2
```

---

---

**Figure 3-20 • Design Example Using Spines of Occupied Global Networks**

## Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

## Related Documents

### User's Guides

*IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide*

[http://www.microsemi.com/soc/documents/pa3\\_libguide\\_ug.pdf](http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf)

## FlashROM Support in Flash-Based Devices

The flash FPGAs listed in Table 5-1 support the FlashROM feature and the functions described in this document.

**Table 5-1 • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

*Note:* \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### **IGLOO Terminology**

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### **ProASIC3 Terminology**

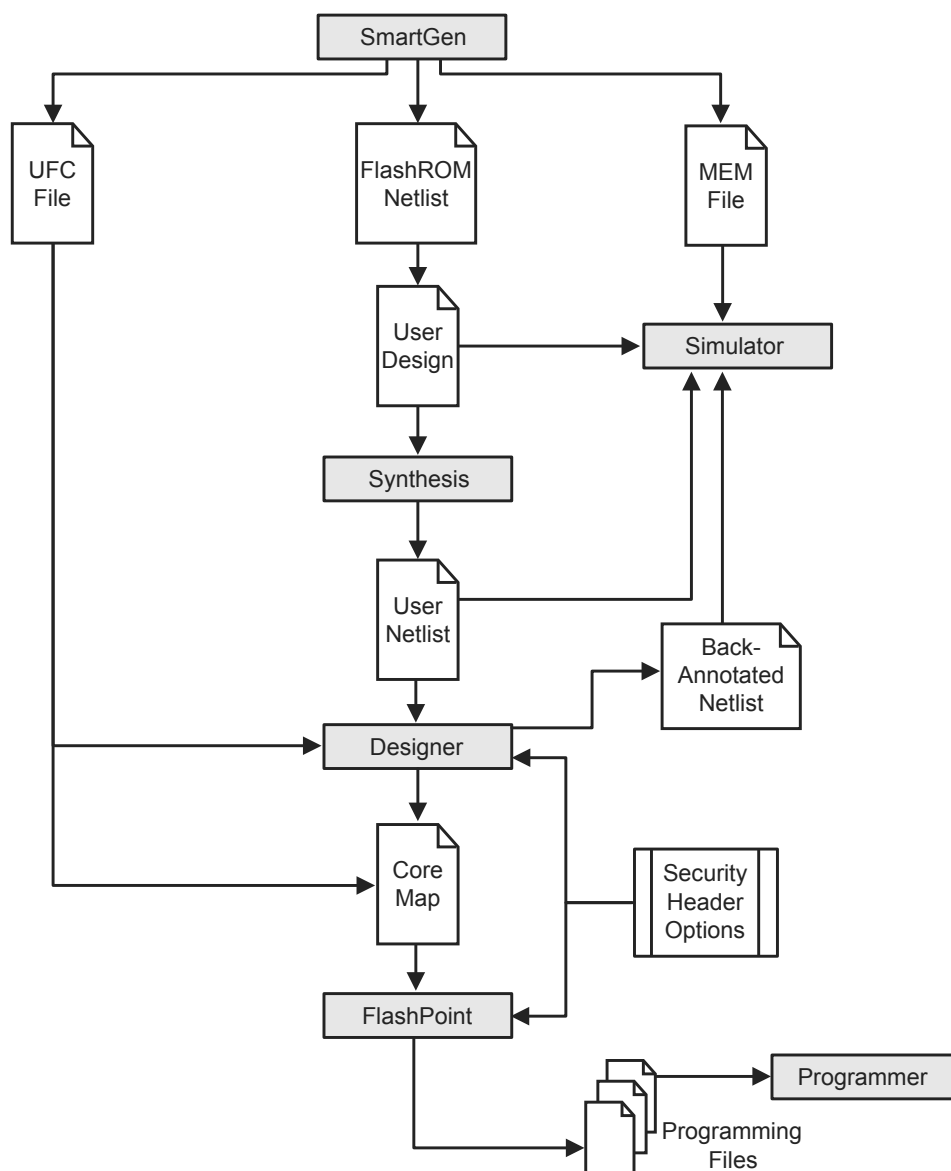
In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

## FlashROM Design Flow

The Microsemi Libero System-on-Chip (SoC) software has extensive FlashROM support, including FlashROM generation, instantiation, simulation, and programming. Figure 5-9 shows the user flow diagram. In the design flow, there are three main steps:

1. FlashROM generation and instantiation in the design
2. Simulation of FlashROM design
3. Programming file generation for FlashROM design



**Figure 5-9 • FlashROM Design Flow**

## SRAM Usage

The following descriptions refer to the usage of both RAM4K9 and RAM512X18.

### Clocking

The dual-port SRAM blocks are only clocked on the rising edge. SmartGen allows falling-edge-triggered clocks by adding inverters to the netlist, hence achieving dual-port SRAM blocks that are clocked on either edge (rising or falling). For dual-port SRAM, each port can be clocked on either edge and by separate clocks by port. Note that for Automotive ProASIC3, the same clock, with an inversion between the two clock pins of the macro, should be used in design to prevent errors during compile.

Low power flash devices support inversion (bubble-pushing) throughout the FPGA architecture, including the clock input to the SRAM modules. Inversions added to the SRAM clock pin on the design schematic or in the HDL code will be automatically accounted for during design compile without incurring additional delay in the clock path.

The two-port SRAM can be clocked on the rising or falling edge of WCLK and RCLK.

If negative-edge RAM and FIFO clocking is selected for memory macros, clock edge inversion management (bubble-pushing) is automatically used within the development tools, without performance penalty.

### Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven onto the RD bus in the same clock cycle following RA and REN valid. The read address is registered on the read port clock active edge, and data appears at RD after the RAM access time. Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from address to data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is HIGH. The setup times of the write address, write enables, and write data are minimal with respect to the write clock.

### RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism. The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

## FIFO Features

The FIFO4KX18 macro is created by merging the RAM block with dedicated FIFO logic (Figure 6-6 on page 158). Since the FIFO logic can only be used in conjunction with the memory block, there is no separate FIFO controller macro. As with the RAM blocks, the FIFO4KX18 nomenclature does not refer to a possible aspect ratio, but rather to the deepest possible data depth and the widest possible data width. FIFO4KX18 can be configured into the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, 512×9, and 256×18. In addition to being fully synchronous, the FIFO4KX18 also has the following features:

- Four FIFO flags: Empty, Full, Almost-Empty, and Almost-Full
- Empty flag is synchronized to the read clock
- Full flag is synchronized to the write clock
- Both Almost-Empty and Almost-Full flags have programmable thresholds
- Active-low asynchronous reset
- Active-low block enable
- Active-low write enable
- Active-high read enable
- Ability to configure the FIFO to either stop counting after the empty or full states are reached or to allow the FIFO counters to continue

## Pipeline Register

```
module D_pipeline (Data, Clock, Q);

input [3:0] Data;
input Clock;
output [3:0] Q;

reg [3:0] Q;

always @ (posedge Clock) Q <= Data;

endmodule
```

## 4x4 RAM Block (created by SmartGen Core Generator)

```
module mem_block(DI,DO,WADDR,RADDR,WRB,RDB,WCLOCK,RCLOCK);

input [3:0] DI;
output [3:0] DO;
input [1:0] WADDR, RADDR;
input WRB, RDB, WCLOCK, RCLOCK;

wire WEBP, WEAP, VCC, GND;

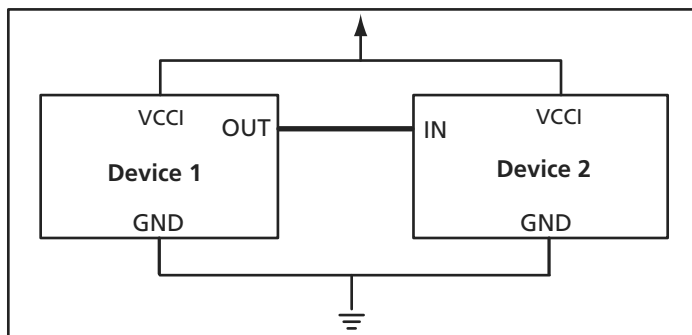
VCC VCC_1_net(.Y(VCC));
GND GND_1_net(.Y(GND));
INV WEBUBBLEB(.A(WRB), .Y(WEBP));
RAM4K9 RAMBLOCK0(.ADDRA11(GND), .ADDRA10(GND), .ADDRA9(GND), .ADDRA8(GND),
    .ADDRA7(GND), .ADDRA6(GND), .ADDRA5(GND), .ADDRA4(GND), .ADDRA3(GND), .ADDRA2(GND),
    .ADDRA1(RADDR[1]), .ADDRA0(RADDR[0]), .ADDRB11(GND), .ADDRB10(GND), .ADDRB9(GND),
    .ADDRB8(GND), .ADDRB7(GND), .ADDRB6(GND), .ADDRB5(GND), .ADDRB4(GND), .ADDRB3(GND),
    .ADDRB2(GND), .ADDRB1(WADDR[1]), .ADDRB0(WADDR[0]), .DINA8(GND), .DINA7(GND),
    .DINA6(GND), .DINA5(GND), .DINA4(GND), .DINA3(GND), .DINA2(GND), .DINA1(GND),
    .DINA0(GND), .DINB8(GND), .DINB7(GND), .DINB6(GND), .DINB5(GND), .DINB4(GND),
    .DINB3(DI[3]), .DINB2(DI[2]), .DINB1(DI[1]), .DINB0(DI[0]), .WIDTHA0(GND),
    .WIDTHA1(VCC), .WIDTHB0(GND), .WIDTHB1(VCC), .PIPEA(GND), .PIPEB(GND),
    .WMODEA(GND), .WMODEB(GND), .BLKA(WEAP), .BLKB(WEBP), .WENA(VCC), .WENB(GND),
    .CLKA(RCLOCK), .CLKB(WCLOCK), .RESET(VCC), .DOUTA8(), .DOUTA7(), .DOUTA6(),
    .DOUTA5(), .DOUTA4(), .DOUTA3(DO[3]), .DOUTA2(DO[2]), .DOUTA1(DO[1]),
    .DOUTA0(DO[0]), .DOUTB8(), .DOUTB7(), .DOUTB6(), .DOUTB5(), .DOUTB4(), .DOUTB3(),
    .DOUTB2(), .DOUTB1(), .DOUTB0());
INV WEBUBBLEA(.A(RDB), .Y(WEAP));

endmodule
```

## I/O Standards

### Single-Ended Standards

These I/O standards use a push-pull CMOS output stage with a voltage referenced to system ground to designate logical states. The input buffer configuration, output drive, and I/O supply voltage (VCCI) vary among the I/O standards (Figure 7-5).



**Figure 7-5 • Single-Ended I/O Standard Topology**

The advantage of these standards is that a common ground can be used for multiple I/Os. This simplifies board layout and reduces system cost. Their low-edge-rate ( $dv/dt$ ) data transmission causes less electromagnetic interference (EMI) on the board. However, they are not suitable for high-frequency (>200 MHz) switching due to noise impact and higher power consumption.

#### **LVTTL (Low-Voltage TTL)**

This is a general-purpose standard (EIA/JESD8-B) for 3.3 V applications. It uses an LVTTL input buffer and a push-pull output buffer. The LVTTL output buffer can have up to six different programmable drive strengths. The default drive strength is 12 mA. VCCI is 3.3 V. Refer to "I/O Programmable Features" on page 188 for details.

#### **LVC MOS (Low-Voltage CMOS)**

The low power flash devices provide four different kinds of LVC MOS: LVC MOS 3.3 V, LVC MOS 2.5 V, LVC MOS 1.8 V, and LVC MOS 1.5 V. LVC MOS 3.3 V is an extension of the LVC MOS standard (JESD8-B-compliant) used for general-purpose 3.3 V applications.

LVC MOS 2.5 V is an extension of the LVC MOS standard (JESD8-5-compliant) used for general-purpose 2.5 V applications.

There is yet another standard supported by IGLOO and ProASIC3 devices (except A3P030): LVC MOS 2.5/5.0 V. This standard is similar to LVC MOS 2.5 V, with the exception that it can support up to 3.3 V on the input side (2.5 V output drive).

LVC MOS 1.8 V is an extension of the LVC MOS standard (JESD8-7-compliant) used for general-purpose 1.8 V applications. LVC MOS 1.5 V is an extension of the LVC MOS standard (JESD8-11-compliant) used for general-purpose 1.5 V applications.

The VCCI values for these standards are 3.3 V, 2.5 V, 1.8 V, and 1.5 V, respectively. Like LVTTL, the output buffer has up to seven different programmable drive strengths (2, 4, 6, 8, 12, 16, and 24 mA). Refer to "I/O Programmable Features" on page 188 for details.

#### **3.3 V PCI (Peripheral Component Interface)**

This standard specifies support for both 33 MHz and 66 MHz PCI bus applications. It uses an LVTTL input buffer and a push-pull output buffer. With the aid of an external resistor, this I/O standard can be 5 V-compliant for low power flash devices. It does not have programmable drive strength.

#### **3.3 V PCI-X (Peripheral Component Interface Extended)**

An enhanced version of the PCI specification, 3.3 V PCI-X can support higher average bandwidths; it increases the speed that data can move within a computer from 66 MHz to 133 MHz. It is backward-



## Compiling the Design

During Compile, a PDC I/O constraint file can be imported along with the netlist file. If only the netlist file is compiled, certain I/O assignments need to be completed before proceeding to Layout. All constraints that can be entered in PDC can also be entered using ChipPlanner, I/O Attribute Editor, and PinEditor.

There are certain rules that must be followed in implementing I/O register combining and the I/O DDR macro (refer to the I/O Registers section of the handbook for the device that you are using and the "DDR" section on page 256 for details). Provided these rules are met, the user can enable or disable I/O register combining by using the PDC command `set_io portname -register yes|no` in the I/O Attribute Editor or selecting a check box in the Compile Options dialog box (see Figure 9-7). The Compile Options dialog box appears when the design is compiled for the first time. It can also be accessed by choosing **Options > Compile** during successive runs. I/O register combining is off by default. The PDC command overrides the setting in the Compile Options dialog box.

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**Figure 9-7 • Setting Register Combining During Compile**

## Understanding the Compile Report

The I/O bank report is generated during Compile and displayed in the log window. This report lists the I/O assignments necessary before Layout can proceed.

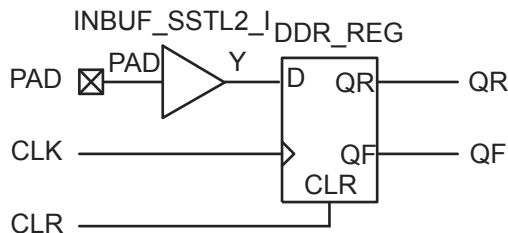
When Designer is started, the I/O Bank Assigner tool is run automatically if the Layout command is executed. The I/O Bank Assigner takes care of the necessary I/O assignments. However, these assignments can also be made manually with MVN or by importing the PDC file. Refer to the "Assigning Technologies and VREF to I/O Banks" section on page 264 for further description.

The I/O bank report can also be extracted from Designer by choosing **Tools > Report** and setting the Report Type to **IOBank**.

This report has the following tables: I/O Function, I/O Technology, I/O Bank Resource Usage, and I/O Voltage Usage. This report is useful if the user wants to do I/O assignments manually.

## Input Support for DDR

The basic structure to support a DDR input is shown in Figure 10-2. Three input registers are used to capture incoming data, which is presented to the core on each rising edge of the I/O register clock. Each I/O tile supports DDR inputs.

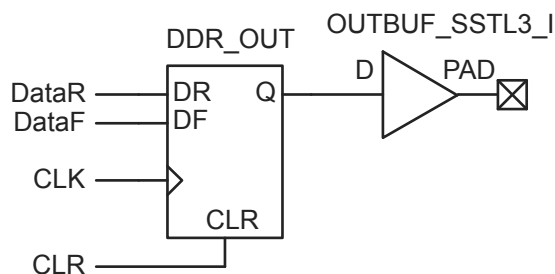


**Figure 10-2 • DDR Input Register Support in Low Power Flash Devices**

## Output Support for DDR

The basic DDR output structure is shown in Figure 10-1 on page 271. New data is presented to the output every half clock cycle.

Note: DDR macros and I/O registers do not require additional routing. The combiner automatically recognizes the DDR macro and pushes its registers to the I/O register area at the edge of the chip. The routing delay from the I/O registers to the I/O buffers is already taken into account in the DDR macro.



**Figure 10-3 • DDR Output Register (SSTL3 Class I)**

## Programming Support in Flash Devices

The flash FPGAs listed in Table 11-1 support flash in-system programming and the functions described in this document.

**Table 11-1 • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution, supporting 1.2 V to 1.5 V core voltage with Flash*Freeze technology
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V core voltage with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
SmartFusion	SmartFusion	Mixed-signal FPGA integrating FPGA fabric, programmable microcontroller subsystem (MSS), including programmable analog and ARM® Cortex™-M3 hard processor and flash memory in a monolithic device
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device
ProASIC	ProASIC	First generation ProASIC devices
	ProASIC <sup>PLUS</sup>	Second generation ProASIC devices

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

## Related Documents

Below is a list of related documents, their location on the Microsemi SoC Products Group website, and a brief summary of each document.

### Application Notes

*Programming Antifuse Devices*

[http://www.microsemi.com/soc/documents/AntifuseProgram\\_AN.pdf](http://www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf)

*Implementation of Security in Actel's ProASIC and ProASIC<sup>PLUS</sup> Flash-Based FPGAs*

[http://www.microsemi.com/soc/documents/Flash\\_Security\\_AN.pdf](http://www.microsemi.com/soc/documents/Flash_Security_AN.pdf)

### User's Guides

#### **FlashPro Programmers**

FlashPro4,<sup>1</sup> FlashPro3, FlashPro Lite, and FlashPro<sup>2</sup>

[http://www.microsemi.com/soc/products/hardware/program\\_debug/flashpro/default.aspx](http://www.microsemi.com/soc/products/hardware/program_debug/flashpro/default.aspx)

*FlashPro User's Guide*

[http://www.microsemi.com/soc/documents/FlashPro\\_UG.pdf](http://www.microsemi.com/soc/documents/FlashPro_UG.pdf)

The FlashPro User's Guide includes hardware and software setup, self-test instructions, use instructions, and a troubleshooting / error message guide.

#### **Silicon Sculptor 3 and Silicon Sculptor II**

[http://www.microsemi.com/soc/products/hardware/program\\_debug/ss/default.aspx](http://www.microsemi.com/soc/products/hardware/program_debug/ss/default.aspx)

### Other Documents

<http://www.microsemi.com/soc/products/solutions/security/default.aspx#flashlock>

The security resource center describes security in Microsemi Flash FPGAs.

*Quality and Reliability Guide*

<http://www.microsemi.com/soc/documents/RelGuide.pdf>

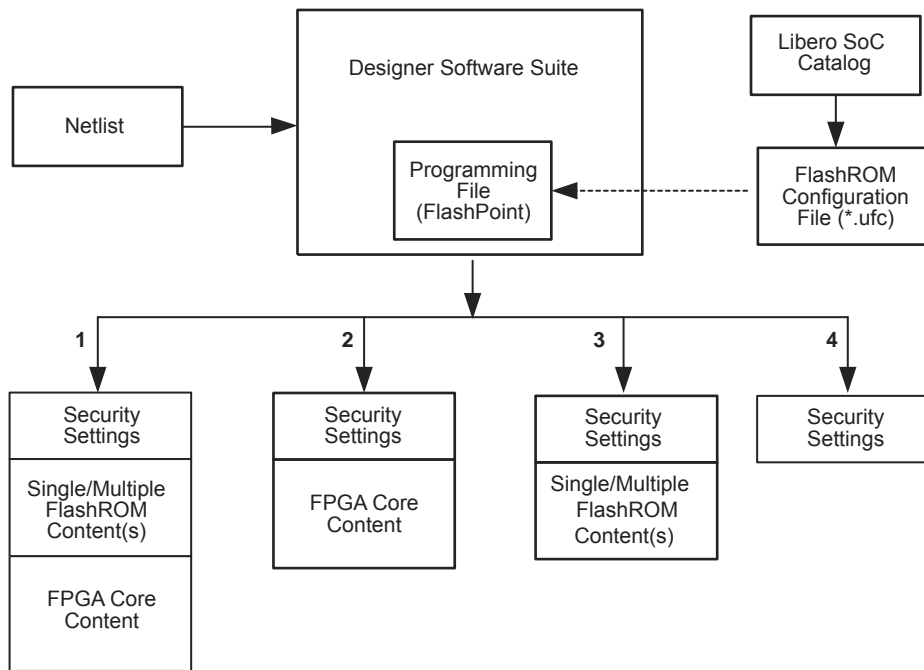
*Programming and Functional Failure Guidelines*

[http://www.microsemi.com/soc/documents/FA\\_Policies\\_Guidelines\\_5-06-00002.pdf](http://www.microsemi.com/soc/documents/FA_Policies_Guidelines_5-06-00002.pdf)

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1. FlashPro4 replaced FlashPro3 in Q1 2010.  
2. FlashPro is no longer available.

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.



**Figure 13-4 • Flexible Programming File Generation for Different Applications**

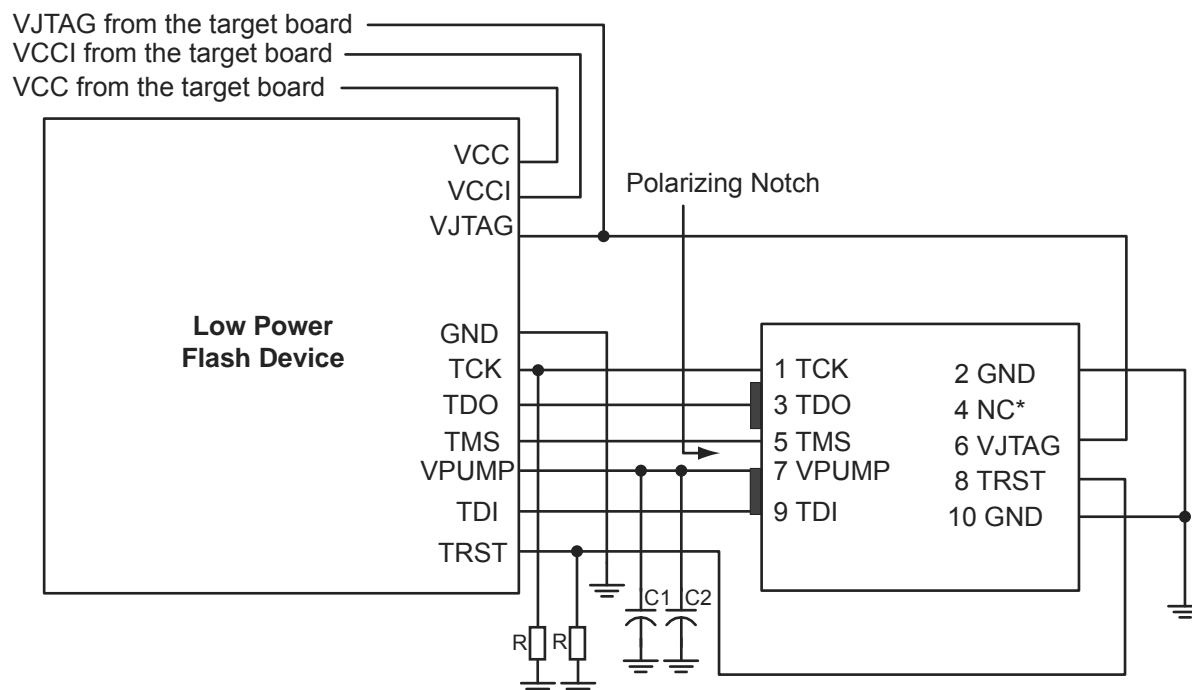
## Programming Solution

For device programming, any IEEE 1532-compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

## Board-Level Considerations

A bypass capacitor is required from VPUMP to GND for all low power flash devices during programming. This bypass capacitor protects the devices from voltage spikes that may occur on the VPUMP supplies during the erase and programming cycles. Refer to the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for specific recommendations. For proper programming, 0.01  $\mu\text{F}$  and 0.33  $\mu\text{F}$  capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible. The bypass capacitor must be placed within 2.5 cm of the device pins.



**Note:** \*NC (FlashPro3/3X); Prog\_Mode (FlashPro4). Prog\_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

**Figure 13-6 • Board Layout and Programming Header Top View**

## Troubleshooting Signal Integrity

### Symptoms of a Signal Integrity Problem

A signal integrity problem can manifest itself in many ways. The problem may show up as extra or dropped bits during serial communication, changing the meaning of the communication. There is a normal variation of threshold voltage and frequency response between parts even from the same lot. Because of this, the effects of signal integrity may not always affect different devices on the same board in the same way. Sometimes, replacing a device appears to make signal integrity problems go away, but this is just masking the problem. Different parts on identical boards will exhibit the same problem sooner or later. It is important to fix signal integrity problems early. Unless the signal integrity problems are severe enough to completely block all communication between the device and the programmer, they may show up as subtle problems. Some of the FlashPro4/3/3X exit codes that are caused by signal integrity problems are listed below. Signal integrity problems are not the only possible cause of these

## 16 – Boundary Scan in Low Power Flash Devices

### Boundary Scan

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 16-2 on page 360).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

### TAP Controller State Machine

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 16-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

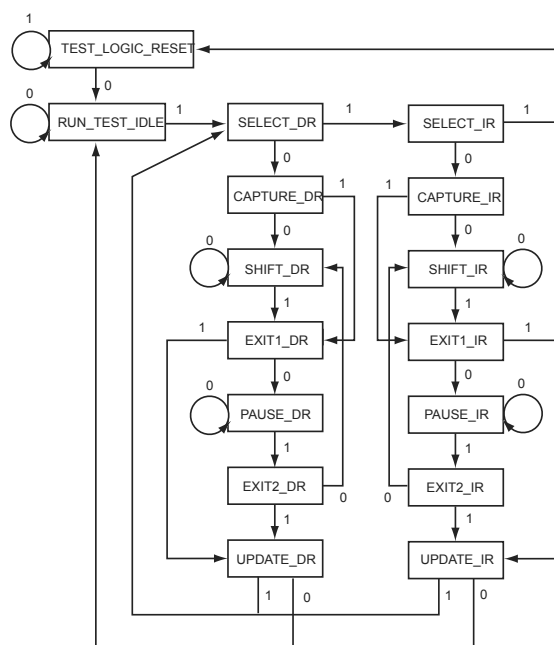


Figure 16-1 • TAP Controller State Machine

## Silicon Testing and Debugging

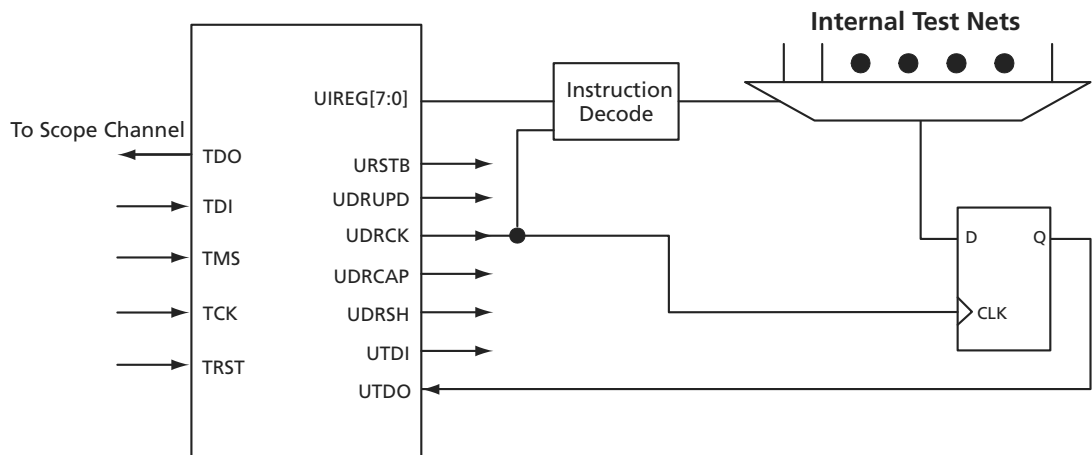
In many applications, the design needs to be tested, debugged, and verified on real silicon or in the final embedded application. To debug and test the functionality of designs, users may need to monitor some internal logic (or nets) during device operation. The approach of adding design test pins to monitor the critical internal signals has many disadvantages, such as limiting the number of user I/Os. Furthermore, adding external I/Os for test purposes may require additional or dedicated board area for testing and debugging.

The UJTAG tiles of low power flash devices offer a flexible and cost-effective solution for silicon test and debug applications. In this solution, the signals under test are shifted out to the TDO pin of the TAP Controller. The main advantage is that all the test signals are monitored from the TDO pin; no pins or additional board-level resources are required. Figure 17-6 illustrates this technique. Multiple test nets are brought into an internal MUX architecture. The selection of the MUX is done using the contents of the TAP Controller instruction register, where individual instructions (values from 16 to 127) correspond to different signals under test. The selected test signal can be synchronized with the rising or falling edge of TCK (optional) and sent out to UTDO to drive the TDO output of JTAG.

For flash devices, TDO (the output) is configured as low slew and the highest drive strength available in the technology and/or device. Here are some examples:

1. If the device is A3P1000 and VCCI is 3.3 V, TDO will be configured as LVTTTL 3.3 V output, 24 mA, low slew.
2. If the device is AGLN020 and VCCI is 1.8 V, TDO will be configured as LVCMOS 1.8 V output, 4 mA, low slew.
3. If the device is AGLE300 and VCCI is 2.5 V, TDO will be configured as LVCMOS 2.5 V output, 24 mA, low slew.

The test and debug procedure is not limited to the example in Figure 17-5 on page 369. Users can customize the debug and test interface to make it appropriate for their applications. For example, multiple test signals can be registered and then sent out through UTDO, each at a different edge of TCK. In other words,  $n$  signals are sampled with an  $F_{TCK} / n$  sampling rate. The bandwidth of the information sent out to TDO is always proportional to the frequency of TCK.



**Figure 17-6 • UJTAG Usage Example in Test and Debug Applications**



Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 0 (continued)	"DDR for Microsemi's Low Power Flash Devices" was revised.	285
	"Programming Flash Devices" was revised.	298
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362